

The EL6F11 is a high - power GaAs IRED mounted in a clear epoxy package. This IRED is both compact and easy to mount.

### FEATURES

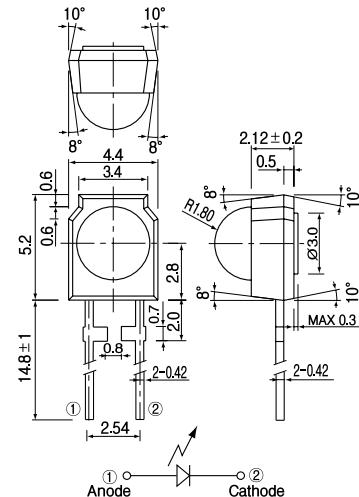
- Plastic mold package with a large caliber lens
- High output power

### APPLICATIONS

- Optical switches

### DIMENSIONS

(Unit : mm)



### MAXIMUM RATINGS

(Ta=25 )

Item	Symbol	Rating	Unit
Reverse voltage	V <sub>R</sub>	4	V
Forward current	I <sub>F</sub>	50	mA
Power dissipation	P <sub>D</sub>	80	mW
Pulse forward current <sup>*1</sup>	I <sub>FP</sub>	1	A
Operating temp.	T <sub>opr.</sub>	- 25 + 85	
Storage temp.	T <sub>stg.</sub>	- 40 + 85	
Soldering temp. <sup>*2</sup>	T <sub>sol.</sub>	260	

<sup>\*1</sup>. pulse width : tw 100  $\mu$ sec.period : T=10msec.

<sup>\*2</sup>. For MAX.5 seconds at the position of 2 mm from the package

### ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25 )

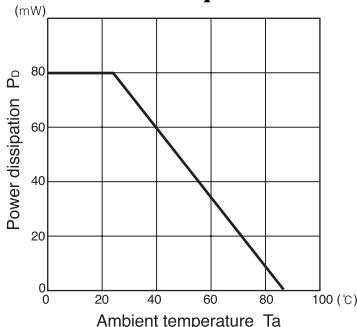
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =50mA		1.3	1.65	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =4V			10	$\mu$ A
Peak emission wavelength	$\lambda$	I <sub>F</sub> =20mA		940		nm
Spectral bandwidth		I <sub>F</sub> =20mA		50		nm
Radiant intensity <sup>*3</sup>	P <sub>O</sub>	I <sub>F</sub> =50mA	2.5	6.0		V
Half angle		I <sub>F</sub> =20mA		$\pm 25$		deg.

<sup>\*3</sup>. Measured by tester of KODENSHI CORP.

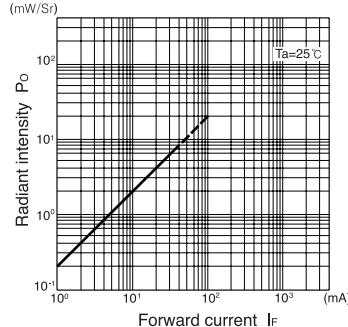
## Infrared Emitting Diodes(GaAs)

EL6F11

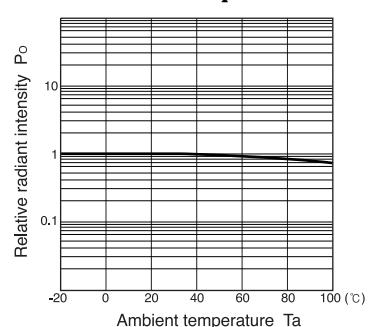
**Power dissipation Vs.  
Ambient temperature**



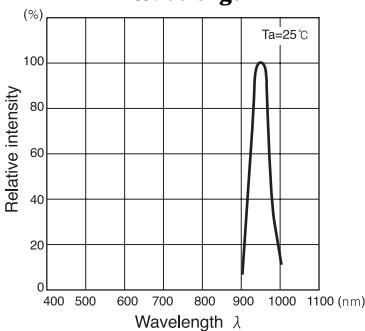
**Radiant intensity Vs.  
Forward current**



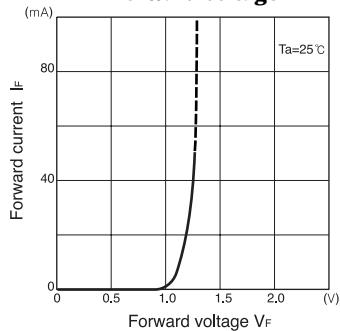
**Relative radiant intensity Vs.  
Ambient temperature**



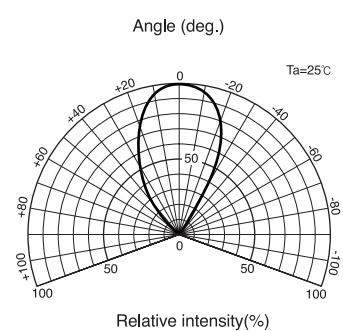
**Relative intensity Vs.  
Wavelength**



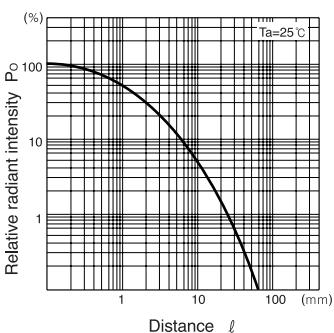
**Forward current vs.  
Forward voltage**



**Radiant Pattern**



**Relative radiant intensity Vs.  
Distance**



Relative radiant intensity Vs.  
Distance test method

